TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE

2SJ440

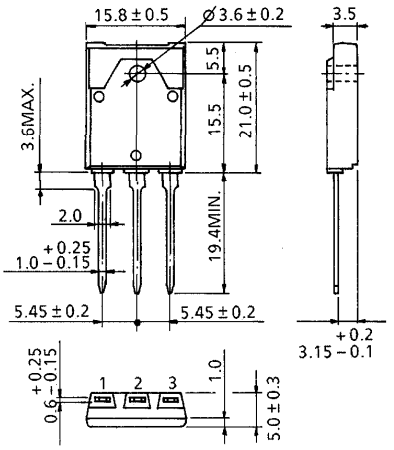
AUDIO FREQUENCY POWER AMPLIFIER APPLICATION

- High Breakdown Voltage : $V_{DSS} = -180$ V
- High Forward Transfer Admittance : $|Y_{fs}| = 4.0$ S (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	−180	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current	I_D	−9	A
Power Dissipation (Tc = 25°C)	P_D	80	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

Unit in mm

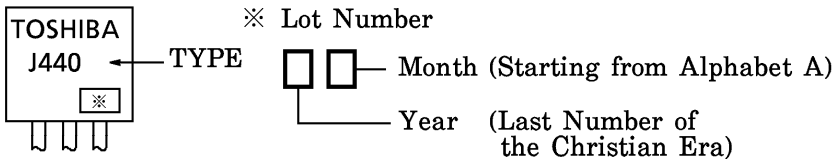


1. GATE
2. DRAIN
3. SOURCE

JEDEC	—
EIAJ	—
TOSHIBA	2-16F1B

Weight : 5.8 g (Typ.)

MARKING



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	V_{DS} = 0, V_{GS} = ±20 V	—	—	±0.5	μA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = −10 mA, V_{GS} = 0	−180	—	—	V
Gate -Source Cut-off Current	$V_{GS(OFF)}$ (Note)	V_{DS} = −10 V, I_D = −0.1 A	−1.4	—	−2.8	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	I_D = −6 A, V_{GS} = −10 V	—	−1.5	−5.0	V
Forward Transfer Admittance	$\|Y_{fs}\|$	V_{DS} = −10 V, I_D = −3 A	—	4.0	—	S
Input Capacitance	C_{iss}	V_{DS} = −30 V, V_{GS} = 0, f = 1 MHz	—	1300	—	pF
Output Capacitance	C_{oss}	V_{DS} = −30 V, V_{GS} = 0, f = 1 MHz	—	350	—	pF
Reverse Transfer Capacitance	C_{rss}	V_{DS} = −30 V, V_{GS} = 0, f = 1 MHz	—	200	—	pF

(Note) : $V_{GS(OFF)}$ Classification Y : −1.4~−2.8

This transistor is the electrostatic sensitive device.
Plese handle with caution.